

September 2009

# MCT2M, MCT2EM, MCT210M, MCT271M Phototransistor Optocouplers

### Features

- UL recognized (File # E90700, Vol. 2)
- IEC60747-5-2 recognized (File # 102497)
  Add option V (e.g., MCT2VM)

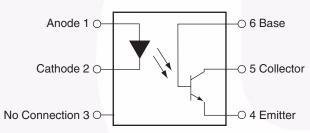
### Applications

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs

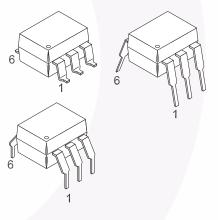
### Description

The MCT2XXM series optoisolators consist of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a 6-pin dual in-line package.

### Schematic



### **Package Outlines**



## **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Value	Units	
TOTAL DEVIC	ČE CONTRACTOR OF C		1	
T <sub>STG</sub>	Storage Temperature	-40 to +150	°C	
T <sub>OPR</sub>	Operating Temperature	-40 to +100	°C	
T <sub>SOL</sub>	Lead Solder Temperature	260 for 10 sec	°C	
PD	Total Device Power Dissipation @ T <sub>A</sub> = 25°C	250	mW	
	Derate above 25°C	2.94	mW/°C	
EMITTER				
I <sub>F</sub>	DC/Average Forward Input Current	60	mA	
V <sub>R</sub>	Reverse Input Voltage	3	V	
l <sub>F</sub> (pk)	Forward Current – Peak (300µs, 2% Duty Cycle)	3	A	
PD	LED Power Dissipation @ T <sub>A</sub> = 25°C	120	mW	
	Derate above 25°C	1.41	mW/°C	
DETECTOR				
Ι <sub>C</sub>	Collector Current	50	mA	
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V	
PD	Detector Power Dissipation @ T <sub>A</sub> = 25°C	150	mW	
	Derate above 25°C	1.76	mW/°C	

Symbol	Parameter	Test Conditions	Device	Min.	Тур.*	Max.	Units
EMITTER	1		I				
V <sub>F</sub>	Input Forward Voltage	I <sub>F</sub> = 20mA	MCT2M MCT2EM MCT271M		1.25	1.50	V
		$T_A = 0^{\circ}C - 70^{\circ}C, I_F = 40mA$	MCT210M		1.33		1
I <sub>R</sub>	Reverse Leakage Current	V <sub>R</sub> = 3.0V	MCT2M MCT2EM MCT271M		0.001	10	μA
		$T_A = 0^{\circ}C - 70^{\circ}C, V_R = 6.0V$	MCT210M				
DETECTO	)R			- /-			
OLO	Collector-Emitter	I <sub>C</sub> = 1.0mA, I <sub>F</sub> = 0	ALL	30	100		V
	Breakdown Voltage	$T_A = 0^{\circ}C - 70^{\circ}C$	MCT210M				
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 10μΑ, I <sub>F</sub> = 0	MCT2M MCT2EM MCT271M	70	120		V
		$T_A = 0^{\circ}C - 70^{\circ}C$	MCT210M	30			
BV <sub>ECO</sub>	Emitter-Collector Breakdown Voltage	I <sub>E</sub> = 100μΑ, I <sub>F</sub> = 0	MCT2M MCT2EM MCT271M	7	10		V
		$T_{A} = 0^{\circ}C - 70^{\circ}C$	MCT210M	6	10		
I <sub>CEO</sub>	Collector-Emitter Dark	V <sub>CE</sub> = 10V, I <sub>F</sub> = 0	ALL		1	50	nA
	Current	$V_{CE} = 5V, T_A = 0^{\circ}C - 70^{\circ}C$				30	μA
I <sub>CBO</sub>	Collector-Base Dark Current	V <sub>CB</sub> = 10V, I <sub>F</sub> = 0	ALL			20	nA
C <sub>CE</sub>	Capacitance	V <sub>CE</sub> = 0V, f = 1MHz	ALL		8		pF

\*All typical  $T_A = 25^{\circ}C$ 

### **Isolation Characteristics**

Symbol	Parameter	Test Conditions	Min	Тур*	Мах	Units
V <sub>ISO</sub>	Input-Output Isolation Voltage	f = 60Hz, t = 1 sec.	7500			Vac(pk)
R <sub>ISO</sub>	Isolation Resistance	V <sub>I-O</sub> = 500 VDC	10 <sup>11</sup>			Ω
C <sub>ISO</sub>	Isolation Capacitance			0.2	2	pF

\*All typicals at  $T_A = 25^{\circ}C$ 

MCT2M, MCT2
Ш
M, MCT210M
0M, MCT271M
1 3 
1

## **Electrical Characteristics** (Continued) ( $T_A = 25^{\circ}C$ unless otherwise specified)

### **Transfer Characteristics**

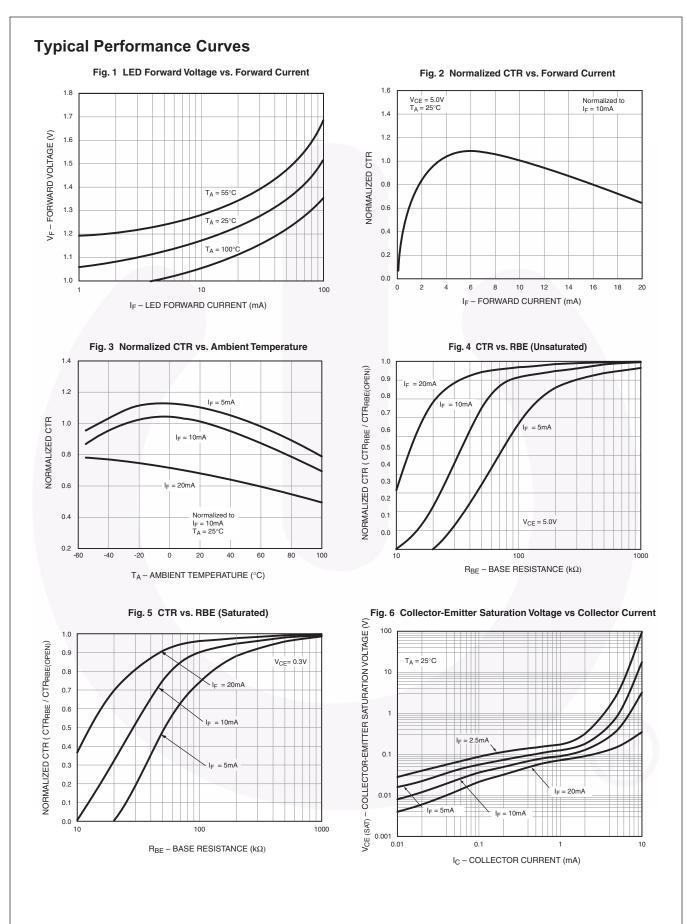
Symbol	Parameter	Test Conditions	Device	Min.	Тур.*	Max.	Unit
DC CHARA	ACTERISTICS						-
CTR	Output Collector	$T_A = 0^{\circ}C - 70^{\circ}C$	MCT210M	150			%
	Current	I <sub>F</sub> = 10mA, V <sub>CE</sub> = 10V	MCT2M MCT2EM	20			]
			MCT271M	45		90	1
		I <sub>F</sub> = 3.2mA to 32mA, V <sub>CE</sub> = 0.4V, T <sub>A</sub> = 0°C–70°C	MCT210M	50			
V <sub>CE(SAT)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2mA, I <sub>F</sub> = 16mA	MCT2M MCT2EM MCT271M			0.4	V
		$I_{C} = 16mA, I_{F} = 32mA,$ $T_{A} = 0^{\circ}C-70^{\circ}C$	MCT210M				
AC CHARA	ACTERISTICS						1
t <sub>on</sub>	AC Characteristic Saturated Turn-on Time from 5V to 0.8V	$I_F$ = 15mA, V <sub>CC</sub> = 5V, R <sub>L</sub> = 2kΩ, R <sub>B</sub> = Open (Fig. 11)	MCT2M MCT2EM		1.1		μs
		$I_F = 20$ mA, $V_{CC} = 5$ V, R <sub>L</sub> = 2kΩ, R <sub>B</sub> = 100kΩ) (Fig. 11)	MCT2M MCT2EM		1.3		
t <sub>off</sub>	Saturated Turn-off Time from SAT to 2.0 V	$I_F$ = 15mA, V <sub>CC</sub> = 5V, R <sub>L</sub> = 2kΩ, R <sub>B</sub> = Open (Fig. 11)	MCT2M MCT2EM		50		μs
		$I_F$ = 20mA, V <sub>CC</sub> = 5V, R <sub>L</sub> = 2kΩ, R <sub>B</sub> = 100kΩ (Fig. 11)	MCT2M MCT2EM		20		
t <sub>on</sub>	Turn-on Time	$I_{F} = 10mA, V_{CC} = 10V,$ $R_{L} = 100\Omega$	MCT2M MCT2EM		2		μs
t <sub>off</sub>	Turn-off Time	$I_{F} = 10mA, V_{CC} = 10V,$ $R_{L} = 100\Omega$	MCT2M MCT2EM		2		μs
t <sub>r</sub>	Rise Time	$I_{F} = 10mA, V_{CC} = 10V,$ $R_{L} = 100\Omega$	MCT2M MCT2EM		2		μs
t <sub>f</sub>	Fall Time	$I_{F} = 10mA, V_{CC} = 10V,$ $R_{L} = 100\Omega$	MCT2M MCT2EM		1.5		μs
t <sub>on</sub>	Saturated turn-on time	I <sub>F</sub> = 16mA, R <sub>L</sub> = 1.9kΩ,	MCT271M		1.0		μs
t <sub>off</sub>	Saturated turn-off time (Approximates a typical TTL interface)	V <sub>CC</sub> = 5V (Fig. 11)			48		μs
t <sub>on</sub>	Saturated turn-on time	I <sub>F</sub> = 16mA, R <sub>L</sub> = 4.7kΩ,	MCT271M		1.0		μs
t <sub>off</sub>	Saturated turn-off time (Approximates a typical low power TTL interface)	V <sub>CC</sub> = 5 V (Fig. 20)			98		μs
t <sub>r</sub>	Saturated rise time	I <sub>F</sub> = 16mA, R <sub>L</sub> = 560Ω,	MCT210M		1.0		μs
t <sub>f</sub>	Saturated fall time	V <sub>CC</sub> = 5V) (Fig. 11, 12)			11		μs
T <sub>PD (HL)</sub>	Saturated propagation delay – HIGH to LOW	I <sub>F</sub> = 16mA, R <sub>L</sub> = 2.7kΩ (Fig. 11, 12)	MCT210M		1.0		μs
T <sub>PD (LH)</sub>	Saturated propagation delay – LOW to HIGH				50		μs
t <sub>r</sub>	Non-saturated rise time	I <sub>C</sub> = 2mA, V <sub>CC</sub> = 5V,	MCT210M		2		μs
t <sub>f</sub>	Non-saturated fall time	$R_{L} = 100\Omega$ (Fig. 11)			2		μs
t <sub>on</sub>	Non-saturated turn-on time	I <sub>C</sub> = 2mA, V <sub>CC</sub> = 5V,	MCT271M		2	7	μs
t <sub>off</sub>	Non-saturated turn-off time	R <sub>L</sub> = 100Ω (Fig. 20)			2	7	μs

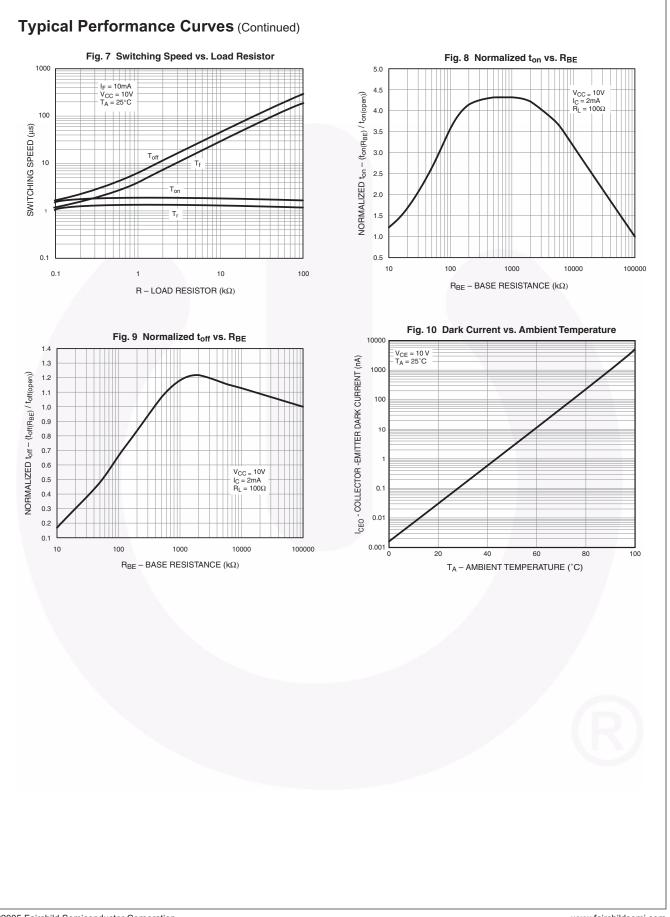
\*All typicals at  $T_A = 25^{\circ}C$ 

## Safety and Insulation Ratings

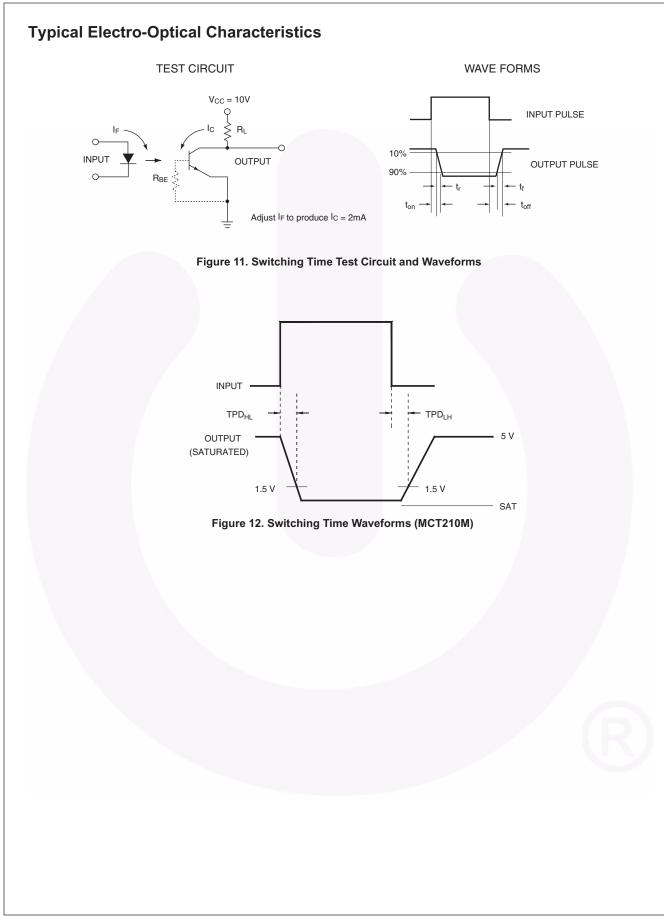
As per IEC 60747-5-2, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Symbol	Parameter	Min.	Тур.	Max.	Unit
	Installation Classifications per DIN VDE 0110/1.89 Table 1				
	For Rated Main Voltage < 150Vrms		I-IV		
	For Rated Main voltage < 300Vrms		I-IV		
	Climatic Classification		55/100/21		
	Pollution Degree (DIN VDE 0110/1.89)		2		
CTI	Comparative Tracking Index	175			
V <sub>PR</sub>	Input to Output Test Voltage, Method b, $V_{IORM} \times 1.875 = V_{PR}$ , 100% Production Test with tm = 1 sec, Partial Discharge < 5pC	1594			V <sub>peak</sub>
	Input to Output Test Voltage, Method a, $V_{IORM} \times 1.5 = V_{PR}$ , Type and Sample Test with tm = 60 sec, Partial Discharge < 5pC				V <sub>peak</sub>
V <sub>IORM</sub>	Max. Working Insulation Voltage	850			V <sub>peak</sub>
V <sub>IOTM</sub>	Highest Allowable Over Voltage	6000			V <sub>peak</sub>
	External Creepage	7			mm
	External Clearance	7			mm
	Insulation Thickness	0.5			mm
RIO	Insulation Resistance at Ts, $V_{IO}$ = 500V	10 <sup>9</sup>			Ω





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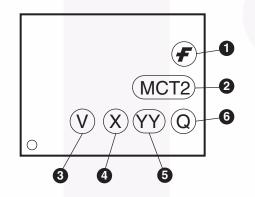


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## **Ordering Information**

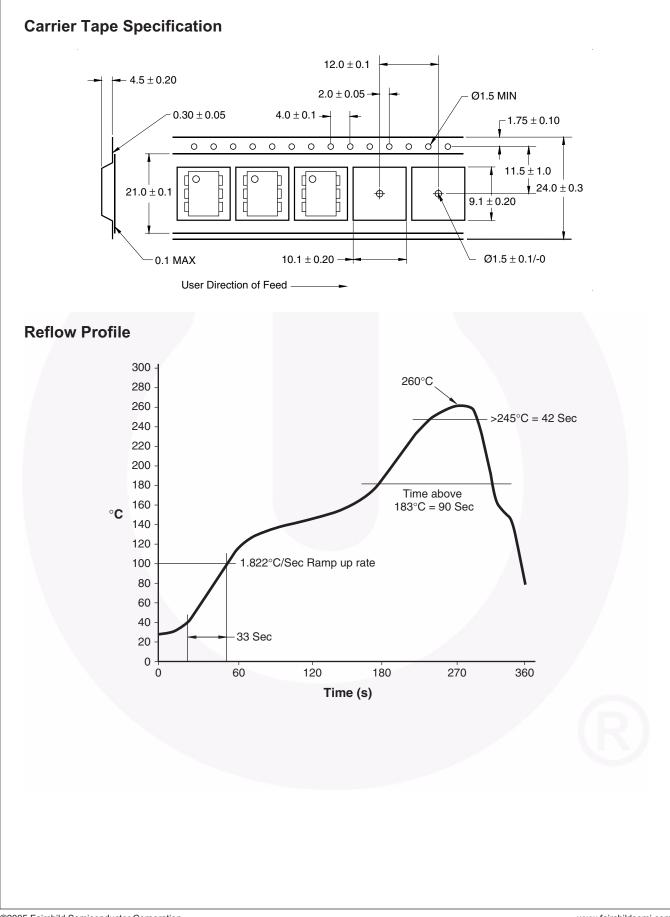
Option	Order Entry Identifier (Example)	Description	
No suffix	MCT2M	Standard Through Hole Device (50 units per tube)	
S	MCT2SM	Surface Mount Lead Bend	
SR2	MCT2SR2M	Surface Mount; Tape and Reel (1,000 units per reel)	
Т	MCT2TM	0.4" Lead Spacing	
V	MCT2VM	IEC60747-5-2	
TV	MCT2TVM	IEC60747-5-2, 0.4" Lead Spacing	
SV	MCT2SVM	IEC60747-5-2, Surface Mount	
SR2V	MCT2SR2VM	IEC60747-5-2, Surface Mount, Tape and Reel (1,000 units per reel)	

# Marking Information



Definitions					
1	Fairchild logo				
2	Device number				
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)				
4	One digit year code, e.g., '7'				
5	Two digit work week ranging from '01' to '53'				
6	Assembly package code				

\*Note – Parts that do not have the 'V' option (see definition 3 above) that are marked with date code '325' or earlier are marked in portrait format.









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Definition of Terms					
Datasheet Identification	Product Status	Definition			
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.			
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.			
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.			
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.			

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